



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Andrew Marshall, et al.

Docket No: TI-31157

Serial No: 10/023,113

Conf. No: 2385

Examiner: Khiem D. Nguyen

Art Unit: 2823

Filed: 12/13/2001

For: MEMORY CELL WITH TRANSISTORS HAVING RELATIVELY HIGH THRESHOLD
VOLTAGES IN RESPONSE TO SELECTIVE GATE DOPING

AMENDMENT UNDER 37 C.F.R. § 1.111

Commissioner For Patents
P.O. Box 1450
Alexandria, VA 22313-1450

MAILING CERTIFICATE UNDER 37 C.F.R. §1.8(a)

I hereby certify that the above correspondence is being deposited with the U.S. Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on 9-5-03.

Ann Trent
Ann Trent

Dear Sir:

Responsive to the Office Action mailed June 5, 2003, in connection with the above identified application, Applicants respectfully submit the following remarks.

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